Features

- Serial Peripheral Interface (SPI) Compatible
- Supports SPI Modes 0 (0,0) and 3 (1,1)
- Data Sheet Describes Mode 0 Operation
- Low-voltage Operation
- 1.8 (V_{cc} = 1.8V to 5.5V)
- 20 MHz Clock Rate (4.5 5.5V)
- 128-byte Page Mode and Byte Write Operation Supported
- Block Write Protection

- Protect 1/4, 1/2, or Entire Array

- Write Protect (WP) Pin and Write Disable Instructions for Both Hardware and Software Data Protection
- Self-timed Write Cycle (5 ms Max)
- High-reliability
 - Endurance: 1 Million Write Cycles
 - Data Retention: >40 Years
- Lead-free/Halogen-free Devices
- 8-lead JEDEC SOIC, 8-lead TSSOP and 8-lead SAP Packages
- Die Sales: Wafer Form, Waffle Pack, and Bumped Die

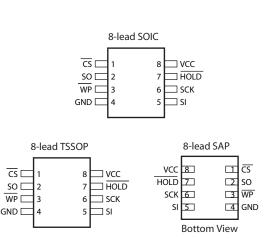
Description

The AT25512 provides 524,288 bits of serial electrically-erasable programmable read only memory (EEPROM) organized as 65,536 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The devices are available in space saving 8-lead JEDEC SOIC, 8-lead TSSOP and 8-lead SAP packages. In addition, the entire family is available in 1.8V (1.8V to 5.5V) versions.

The AT25512 is enabled through the Chip Select pin $\overline{(CS)}$ and accessed via a 3-wire interface consisting of Serial Data Input (SI), Serial Data Output (SO), and Serial Clock (SCK). All programming cycles are completely self-timed, and no separate Erase cycle is required before Write.

Table 0-1. Pin Co	onfigurations
-------------------	---------------

Pin Name	Function
CS	Chip Select
SCK	Serial Data Clock
SI	Serial Data Input
SO	Serial Data Output
GND	Ground
VCC	Power Supply
WP	Write Protect
HOLD	Suspends Serial Input
NC	No Connect





SPI Serial EEPROM

512K (65,536 x 8)

AT25512

5165F-SEEPR-3/09

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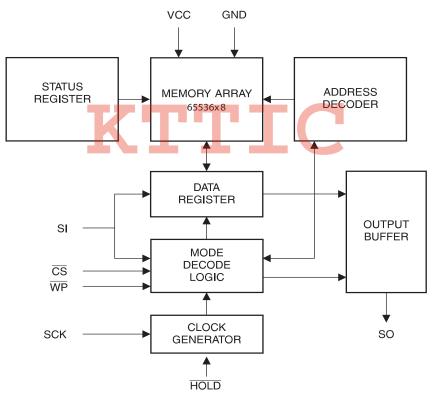
Block Write protection is enabled by programming the status register with top ¼, top ½ or entire array of write protection. Separate Program Enable and Program Disable instructions are provided for additional data protection. Hardware data protection is provided via the WP pin to protect against inadvertent write attempts to the status register. The HOLD pin may be used to suspend any serial communication without resetting the serial sequence.

1. Absolute Maximum Ratings*

Operating Temperature55°C to +125°C	*
Storage Temperature65°C to +150°C	
Voltage on Any Pin with Respect to Ground1.0V to +7.0V	
Maximum Operating Voltage 6.25V	
DC Output Current 5.0 mA	

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 1-1. Block Diagram



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Table 1-1.Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^{\circ}C$, f = 1.0 MHz, $V_{CC} = +5.0V$ (unless otherwise noted)

Symbol	Test Conditions	Max	Units	Conditions
C _{OUT}	Output Capacitance (SO)	8	pF	V _{OUT} = 0V
C _{IN}	Input Capacitance (CS, SCK, SI, WP, HOLD)	6	pF	$V_{IN} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.

Table 1-2.DC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}C$ to +85°C, $V_{CC} = +1.8V$ to +5.5V, $V_{CC} = +1.8V$ to +5.5V(unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Тур	Max	Units
V _{CC1}	Supply Voltage		1.8		5.5	V	
V _{CC2}	Supply Voltage			2.7		5.5	V
V _{CC3}	Supply Voltage			4.5		5.5	V
I _{CC1}	Supply Current	V _{CC} = 5.0V at 20 MI Read	Hz, SO = Open,		9.0	10.0	mA
I _{CC2}	Supply Current		V _{CC} = 5.0V at 10 MHz, SO = Open, Read, Write			7.0	mA
I _{CC3}	Supply Current	V _{CC} = 5.0V at 1 MH SO = Open, Read, V		2.2	3.5	mA	
I _{SB1}	Standby Current	$V_{CC} = 1.8V, \overline{CS} = V_{CC}$	$V_{cc} = 1.8V, \overline{CS} = V_{cc}$			3.0	μA
I _{SB2}	Standby Current	$V_{CC} = 2.7V, \overline{CS} = V_{CC}$	$V_{cc} = 2.7V, \overline{CS} = V_{cc}$			3.0	μA
I _{SB3}	Standby Current	$V_{CC} = 5.0V, \overline{CS} = V_{CC}$	c		2.0	5.0	μA
I _{IL}	Input Leakage	V_{IN} = 0V to V_{CC}		-3.0		3.0	μA
I _{OL}	Output Leakage	$V_{IN} = 0V$ to V_{CC} , T_{AC}	; = 0·C to 70·C	-3.0		3.0	μA
V _{IL} ⁽¹⁾	Input Low-voltage			-1.0		V _{CC} x 0.3	V
V _{IH} ⁽¹⁾	Input High-voltage			V _{CC} x 0.7		V _{CC} + 0.5	V
V _{OL1}	Output Low-voltage		I _{OL} = 3.0 mA			0.4	V
V _{OH1}	Output High-voltage	$3.6 \le V_{CC} \le 5.5V$	I _{OH} = -1.6 mA	V _{CC} –0.8			V
V _{OL2}	Output Low-voltage		I _{OL} = 0.15 mA			0.2	V
V _{OH2}	Output High-voltage	$1.8V \le V_{CC} \le 3.6V$	I _{OH} = -100 μA	V _{CC} –0.2			V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.



Table 1-3.AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40 \cdot C$ to + 85·C, V_{CC} = As Specified, CL = 1 TTL Gate and 30 pF (unless otherwise noted)

Symbol	Parameter	Voltage	Min	Max	Units
f _{SCK}	SCK Clock Frequency	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0	20 10 5	MHz
t _{RI}	Input Rise Time	4.5–5.5 2.7–5.5 1.8–5.5		2 2 2	μs
t _{FI}	Input Fall Time	4.5–5.5 2.7–5.5 1.8–5.5		2 2 2	μs
t _{WH}	SCK High Time	4.5–5.5 2.7–5.5 1.8–5.5	20 40 80		ns
t _{WL}	SCK Low Time	4.5–5.5 2.7–5.5 1.8–5.5	20 40 80		ns
t _{cs}	CS High Time	4.5–5.5 2.7–5.5 1.8–5.5	100 100 200		ns
t _{css}	CS Setup Time	4.5–5.5 2.7–5.5 1.8–5.5	100 100 200		ns
t _{CSH}	CS Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	100 100 200		ns
t _{SU}	Data In Setup Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		ns
t _H	Data In Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		ns
t _{HD}	Hold Setup Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		ns
t _{CD}	Hold Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		ns
t _v	Output Valid	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0	20 40 80	ns
t _{HO}	Output Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0		ns
t _{LZ}	Hold to Output Low Z	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0	25 50 100	ns

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 Table 1-3.
 AC Characteristics (Continued)

Applicable over recommended operating range from $T_{AI} = -40 \cdot C$ to + 85 $\cdot C$, V_{CC} = As Specified, CL = 1 TTL Gate and 30 pF (unless otherwise noted)

Symbol	Parameter	Voltage	Min	Max	Units	
t _{HZ} Hold to Output High Z		4.5–5.5 2.7–5.5 1.8–5.5	25 50 100		ns	
t _{DIS}	Output Disable Time	4.5–5.5 2.7–5.5 1.8–5.5		25 50 100	ns	
t _{wc}	Write Cycle Time	4.5–5.5 2.7–5.5 1.8–5.5		5 5 5	ms	
Endurance ⁽¹⁾	5.0V, 25·C, Page Mode		1M		Write Cycles	

Notes: 1. This parameter is characterized and is not 100% tested. Contact Atmel for further information.

2. Serial Interface Description

MASTER: The device that generates the serial clock.

SLAVE: Because the serial clock pin (SCK) is always an input, the AT25512 always operates as a slave.

TRANSMITTER/RECEIVER: The AT25512 has separate pins designated for data transmission (SO) and reception (SI).

MSB: The Most Significant Bit (MSB) is the first bit transmitted and received.

SERIAL OP-CODE: After the device is selected with \overline{CS} going low, the first byte will be received. This byte contains the op-code that defines the operations to be performed.

INVALID OP-CODE: If an invalid op-code is received, no data will be shifted into the AT25512, and the serial output pin (SO) will remain in a high impedance state until the falling edge of \overline{CS} is detected again. This will reinitialize the serial communication.

CHIP SELECT: The AT25512 is selected when the \overline{CS} pin is low. When the device is not selected, data will not be accepted via the SI pin, and the serial output pin (SO) will remain in a high impedance state.

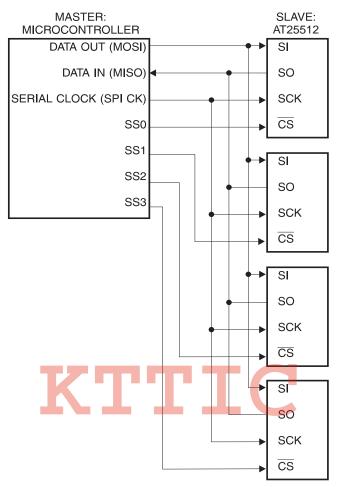
HOLD: The HOLD pin is used in conjunction with the \overline{CS} pin to select the AT25512. When the device is selected and a serial sequence is underway, HOLD can be used to pause the serial communication with the master device without resetting the serial sequence. To pause, the HOLD pin must be brought low while the SCK pin is low. To resume serial communication, the HOLD pin is brought high while the SCK pin is low (SCK may still toggle during HOLD). Inputs to the SI pin will be ignored while the SO pin is in the high impedance state.

WRITE PROTECT: The write protect pin (\overline{WP}) will allow normal read/write operations when held high. When the \overline{WP} pin is brought low and WPEN bit is "1", all write operations to the status register are inhibited. \overline{WP} going low while \overline{CS} is still low will interrupt a write to the status register. If the internal write cycle has already been initiated, \overline{WP} going low will have no effect on any write operation to the status register. The \overline{WP} pin function is blocked when the WPEN bit in the status register is "0". This will allow the user to install the AT25512 in a system with the \overline{WP} pin tied to



ground and still be able to write to the status register. All $\overline{\text{WP}}$ pin functions are enabled when the WPEN bit is set to "1".

Figure 2-1. SPI Serial Interface



3. Functional Description

The AT25512 is designed to interface directly with the synchronous serial peripheral interface (SPI) of the 6800 type series of microcontrollers.

The AT25512 utilizes an 8-bit instruction register. The list of instructions and their operation codes are contained in see Table 4-3. All instructions, addresses, and data are transferred with the MSB first and start with a high-to-low \overline{CS} transition.

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Instruction Name	Instruction Format	Operation
WREN	0000 X110	Set Write Enable Latch
WRDI	0000 X100	Reset Write Enable Latch
RDSR	0000 X101	Read Status Register
WRSR	0000 X001	Write Status Register
READ	0000 X011	Read Data from Memory Array
WRITE	0000 X010	Write Data to Memory Array

Table 3-1.Instruction Set for the AT25512

WRITE ENABLE (WREN): The device will power-up in the write disable state when V_{CC} is applied. All programming instructions must therefore be preceded by a Write Enable instruction.

WRITE DISABLE (WRDI): To protect the device against inadvertent writes, the Write Disable instruction disables all programming modes. The WRDI instruction is independent of the status of the WP pin.

READ STATUS REGISTER (RDSR): The Read Status Register instruction provides access to the status register. The Ready/Busy and Write Enable status of the device can be determined by the RDSR instruction. Similarly, the Block Write Protection bits indicate the extent of protection employed. These bits are set by using the WRSR instruction.

 Table 3-2.
 Status Register Format

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
WPEN	X	Х	Х	BP1	BP0	WEN	RDY

Table 3-3. Read Status Register Bit Definition

Bit	Definition		
Bit 0 (RDY)	Bit $0 = "0" (\overline{RDY})$ indicates the device is ready. Bit $0 = "1"$ indicates the write cycle is in progress.		
Bit 1 (WEN)	Bit $1 = 0$ indicates the device <i>is not</i> write enabled. Bit $1 = "1"$ indicates the device is write enabled.		
Bit 2 (BP0)	See Table 3-4 on page 8.		
Bit 3 (BP1)	See Table 3-4 on page 8.		
Bits 4 – 6 are 0s whe	en device is not in an internal write cycle.		
Bit 7 (WPEN) See Table 3-5 on page 8.			
Bits 0 – 7 are "1"s du	iring an internal write cycle.		

WRITE STATUS REGISTER (WRSR): The WRSR instruction allows the user to select one of four levels of protection. The AT25512 is divided into four array segments. Top quarter (1/4), top half (1/2), or all of the memory segments can be protected. Any of the data within any selected segment will therefore be read only. The block write protection levels and corresponding status register control bits are shown in Table 3-4.

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The three bits, BP0, BP1, and WPEN are nonvolatile cells that have the same properties and functions as the regular memory cells (e.g. WREN, t_{WC} , RDSR).

	Status Re	gister Bits	Array Addresses Protected
Level	BP1	BP0	AT25512
0	0	0	None
1(1/4)	0	1	C000 – FFFF
2(1/2)	1	0	8000 – FFFF
3(All)	1	1	0000 – FFFF

 Table 3-4.
 Block Write Protect Bits

The WRSR instruction also allows the user to enable or disable the write protect (\overline{WP}) pin through the use of the write protect enable (WPEN) bit. Hardware write protection is enabled when the \overline{WP} pin is low and the WPEN bit is "1". Hardware write protection is disabled when *either* the \overline{WP} pin is high or the WPEN bit is "0". When the device is hardware write protected, writes to the Status Register, including the Block Protect bits and the WPEN bit, and the block-protected sections in the memory array are disabled. Writes are only allowed to sections of the memory which are not block-protected.

NOTE: When the WPEN bit is hardware write protected, it cannot be changed back to "0", as long as the \overline{WP} pin is held low.

WPEN	WP	WEN	Prote <mark>ct</mark> ed Blocks	Unprotected Blocks	Status Register
0	Х	0	Protected	Protected	Protected
0	Х	1	Protected	Writable	Writable
1	Low	0	Protected	Protected	Protected
1	Low	1	Protected	Writable	Protected
Х	High	0	Protected	Protected	Protected
Х	High	1	Protected	Writable	Writable

Table 3-5. WPEN Operation

READ SEQUENCE (**READ**): Reading the AT25512 via the SO pin requires the following sequence. After the \overline{CS} line is pulled low to select a device, the Read op-code is transmitted via the SI line followed by the byte address to be read (see Table 3-6 on page 9). Upon completion, any data on the SI line will be ignored. The data (D7 – D0) at the specified address is then shifted out onto the SO line. If only one byte is to be read, the \overline{CS} line should be driven high after the data comes out. The read sequence can be continued since the byte address is reached, the address counter will continue to be shifted out. When the highest address is reached, the address counter will roll over to the lowest address allowing the entire memory to be read in one continuous read cycle.

WRITE SEQUENCE (WRITE): In order to program the AT25512, two separate instructions must be executed. First, the device *must be write enabled* via the Write Enable (WREN) Instruction. Then a Write instruction may be executed. Also, the address of the memory location(s) to be programmed must be outside the protected address field location selected by the Block Write

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Protection Level. During an internal write cycle, all commands will be ignored except the RDSR instruction.

A Write Instruction requires the following sequence. After the \overline{CS} line is pulled low to select the device, the Write op-code is transmitted via the SI line followed by the byte address and the data (D7 – D0) to be programmed (see Table 3-6). Programming will start after the \overline{CS} pin is brought high. (The Low-to-High transition of the \overline{CS} pin must occur during the SCK low time immediately after clocking in the D0 (LSB) data bit.

The Ready/Busy status of the device can be determined by initiating a Read Status Register (RDSR) Instruction. If Bit 0 = 1, the Write cycle is still in progress. If Bit 0 = 0, the Write cycle has ended. Only the Read Status Register instruction is enabled during the Write programming cycle.

The AT25512 is capable of a 128-byte Page Write operation. After each byte of data is received, the seven low order address bits are internally incremented by one; the high order bits of the address will remain constant. If more than 128 bytes of data are transmitted, the address counter will roll over and the previously written data will be overwritten. The AT25512 is automatically returned to the write disable state at the completion of a Write cycle.

NOTE: If the device is not write enabled (WREN), the device will ignore the Write instruction and will return to the standby state, when \overline{CS} is brought high. A new CS falling edge is required to re-initiate the serial communication.

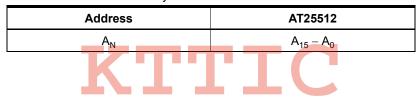
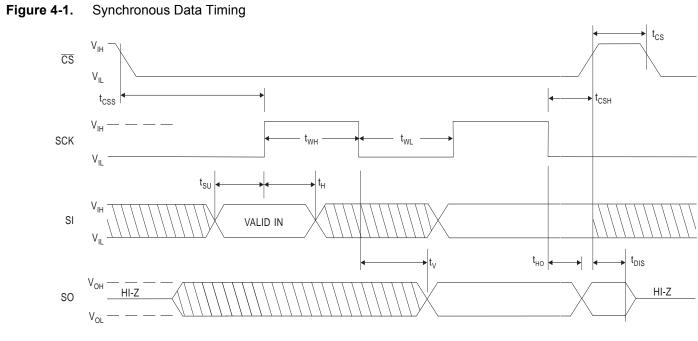
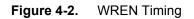


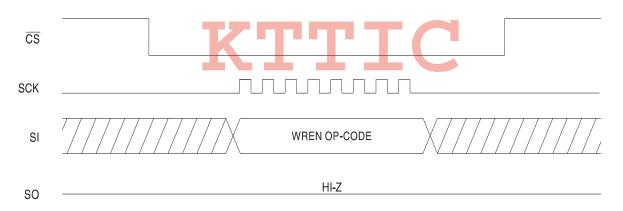
Table 3-6.Address Key



4. Timing Diagrams (for SPI Mode 0 (0, 0))



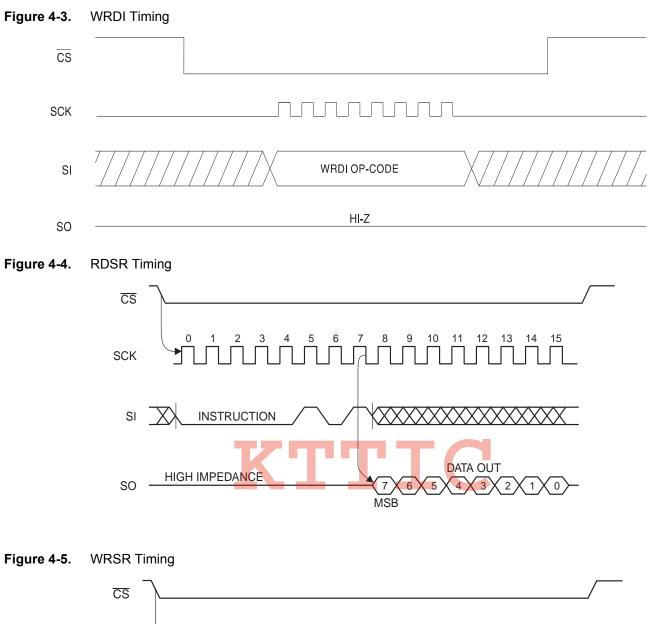


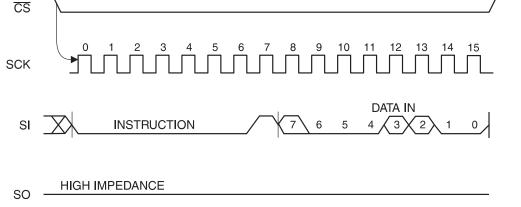


AT25512

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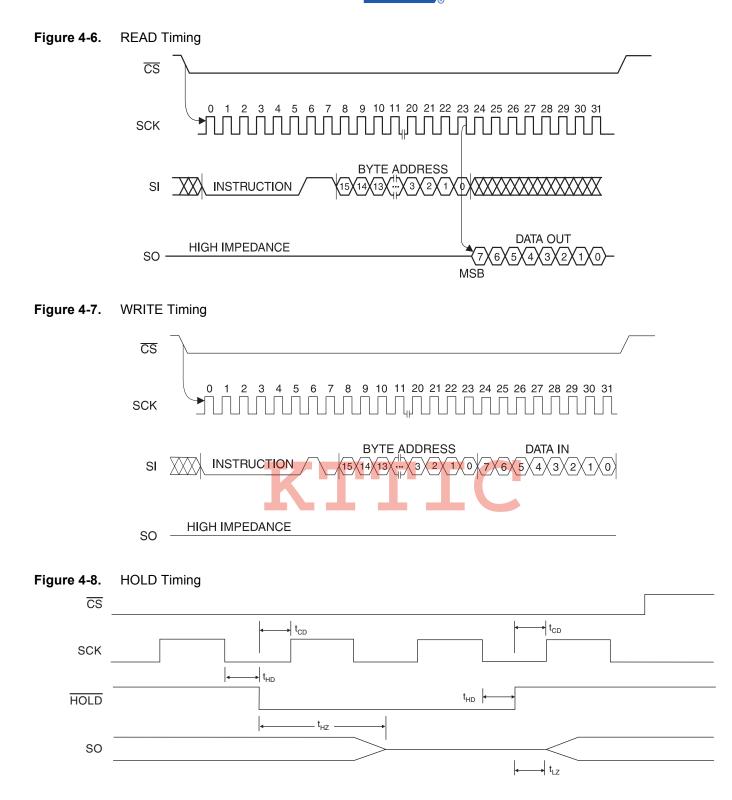
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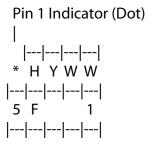


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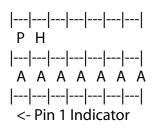


5. Part Marking Scheme

TOP MARK



BOTTOM MARK



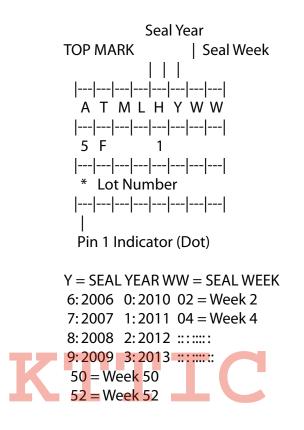
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6:2006	0:2010	02 =	= W <mark>e</mark>	ek 2		
7:2007	1:2011	04 =	= We	ek 4		
8:2008	2:2012					
9:2009	3:2013		:::			
50 = We	eek 50					

52 = Week 52



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AT25512N-SH-B/T



Lot Number to Use ALL Characters in Marking

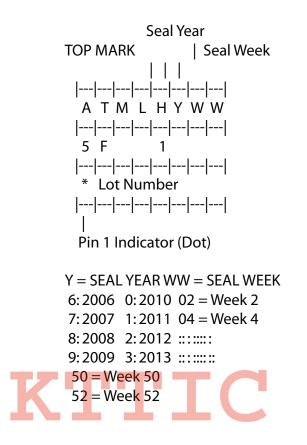
BOTTOM MARK

No Bottom Mark

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AT25512

AT25512Y7-YH-T



Lot Number to Use ALL Characters in Marking

BOTTOM MARK

No Bottom Mark





6. AT25512 Ordering Information

Ordering Code	Voltage	Package	Operation Range
AT25512N-SH-B ⁽¹⁾	1.8	8S1	
AT25512N-SH-T ⁽²⁾	1.8	8S1	Lead-free/Halogen-free
AT25512-TH-B ⁽¹⁾	1.8	8A2	NiPDAu Lead Finish
AT25512-TH-T ⁽²⁾	1.8	8A2	Industrial Temperature
AT25512Y7-YH-T ⁽²⁾	1.8	8Y7	(–40°C to 85°C)
AT25512-W-11 ⁽³⁾	1.8	Die Sale	Industrial Temperature
			(–40°C to 85°C)

Notes: 1. "-B" denotes bulk.

- 2. "-T" denotes tape and reel. SOIC = 4K per reel. TSSOP = 5K per reel. SAP = 3K per reel.
- 3. Available in waffle pack, tape and reel, and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

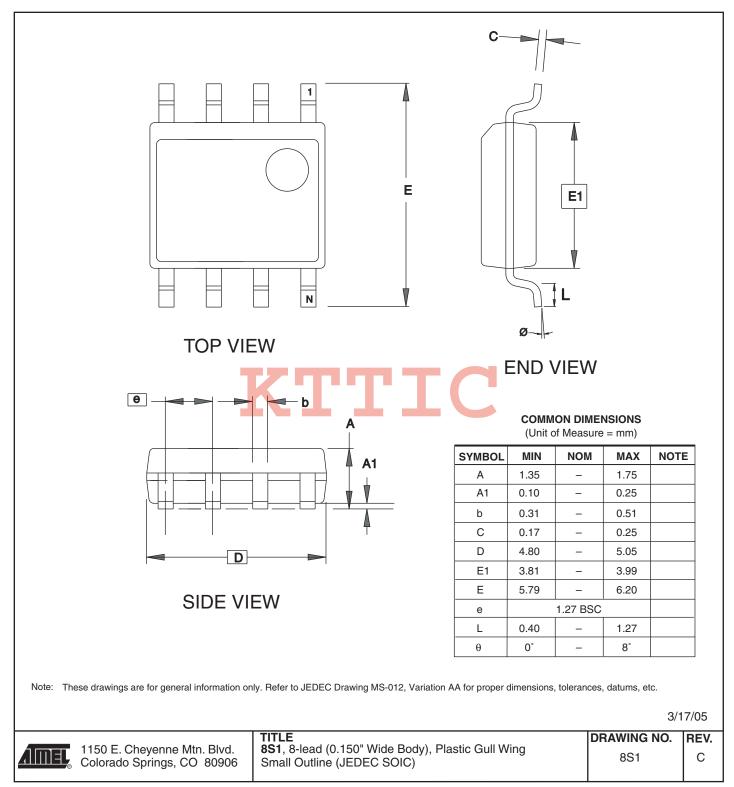
KTTIC

Package Type				
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)			
8A2	8-lead, 4.4 mm Body, Plastic Thin Shrink Small Outline Package (TSSOP)			
8Y7	8-lead, 6.00mm x 4.90mm Body, Ultra Thin, Dual Footprint, Non-leaded, Small Array Package (SAP)			
Options				
-1.8	Low-voltage (1.8V to 5.5V)			

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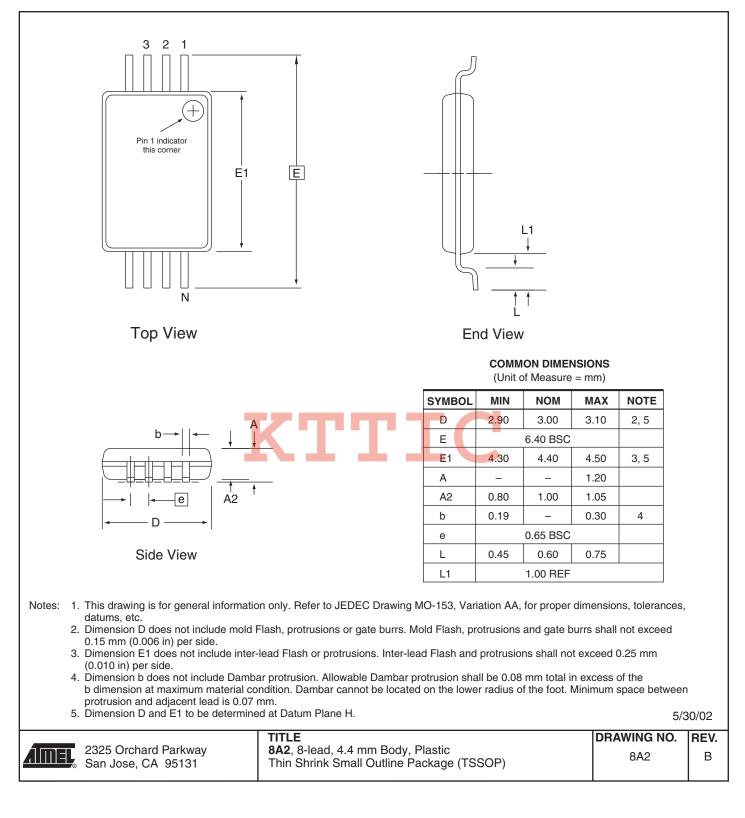
7. Packaging Information

8S1 – JEDEC SOIC

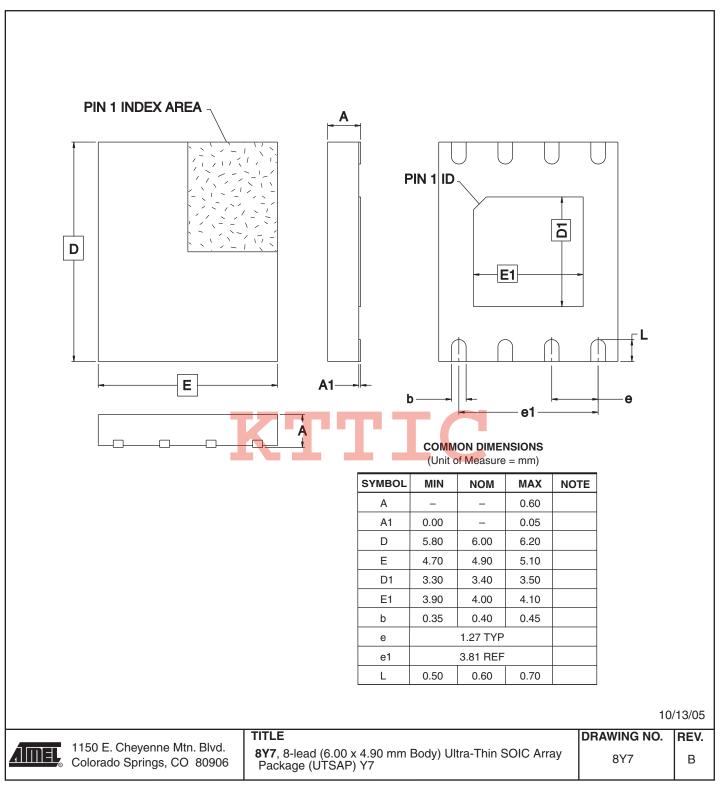




8A2 – TSSOP



8Y7 - SAP





8. Revision History

Doc. Rev.	Date	Comments	
5165F 3/2009		Changed Maximum Operating Voltage from 4.3V to 6.25V in the Absolute Maximum Ratings Table on page 2	
5165E	8/2008	Updated for 1.8V - 5.5V operation	
5165D	5/2008	Added part marking diagram information	
5165C	8/2007	Changed address bit number to seven on page 9 Removed Preliminary status	
5165B	6/2007	Changed spacing on table notes Reworked figure 4-8 Updated to new template Changed status to Preliminary	
5165A	1/2007	Initial document release	

KTTIC